

International application No.
PCT/JP03/08333

A. CLASS	SIFICATION OF SUBJECT MATTER C1 ⁷ H01L21/322, H01L27/12, C30	B29/06		
According t	o International Patent Classification (IPC) or to both na	tional classification and IPC		
B. FIELD	S SEARCHED			
Minimum d Int.	ocumentation searched (classification system followed l C1 ⁷ H01L21/26-21/268, H01L21/3 H01L21/205, C30B1/00-35/00	22-21/326, H01L27/12,	·	
Jitsı Koka:	tion searched other than minimum documentation to the Layo Shinan Koho 1922–1996 i Jitsuyo Shinan Koho 1971–2003	Toroku Jitsuyo Shinan Koho Jitsuyo Shinan Toroku Koho	1994–2003 1996–2003	
Electronic d	ata base consulted during the international search (nam	e of data base and, where practicable, sear	rch terms used)	
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C. DOCU	MENTS CONSIDERED TO BE RELEVANT			
Category*	Citation of document, with indication, where ap	propriate, of the relevant passages	Relevant to claim No.	
Y A	EP 1087041 A1 (SHIN-ETSU HAN 28 March, 2001 (28.03.01), Full text; Figs. 1 to 5 & WO 00/55397 A1 Full text; Figs. 1 to 5	DOTAI CO., LTD.), 6544656 B1	1-8,10-17 9	
Y A	BABICH, V.M. et al., 'Generat donors as a result of one- an of silicon crystals with larg concentraions', Semiconductor May 1996, pages 417 to 419	nd two-step annealing ge and small carbon	1-8,10-17 9	
	de constant de l'atad in the continuation of Post C	See patent family annex.		
"A" document defining the general state of the art which is not considered to be of particular relevance "E" earlier document but published on or after the international filing date document which may throw doubts on priority claim(s) or which is cited to establish the publication date of another citation or other special reason (as specified) document referring to an oral disclosure, use, exhibition or other means document published prior to the international filing date but later than the priority date claimed		"T" later document published after the international filing date or priority date and not in conflict with the application but cited to understand the principle or theory underlying the invention document of particular relevance; the claimed invention cannot be considered novel or cannot be considered to involve an inventive step when the document is taken alone document of particular relevance; the claimed invention cannot be considered to involve an inventive step when the document is combined with one or more other such documents, such combination being obvious to a person skilled in the art document member of the same patent family		
30 S	actual completion of the international search eptember, 2003 (30.09.03)	Date of mailing of the international sear 21 October, 2003 (2	ch report 21.10.03)	
Name and m Japa	nailing address of the ISA/ nese Patent Office	Authorized officer		
Facsimile No.		Telephone No.		



INTERNATIONAL SEARCH REPORT

International application No. PCT/JP03/08333

Category*	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No
Y	KODATE, Jun'ichi et al., 'Suppression of Substrate Crosstalk in Mixed-Signal Complementary MOS Circuits Using High-Resistivity SIMOX (Separation by IMplanted OXygen) Wafers', Japanese Journal of Applied Physics, Part 1, Vol.39, No.4B, April 2000, pages 2256 to 2260	7,14,15
Y	JP 5-144827 A (Komatsu Electronic Metals Co., Ltd.), 11 June, 1993 (11.06.93), Full text; Figs. 1 to 3 & WO 93/10557 A1	13
A	WIJARANAKULA, W. et al., 'A Formation of Crystal Defects in Carbon-Doped Czochralski-Grown Silicon after a Three-Step Internal Gettering Anneal', Journal of Electrochemical Society, Vol.138, No.7, July 1991, pages 2153 to 2159	1-17
A	GAWORZEWSKI P. et al., 'Oxygen-Related Donors Formed at 600°C in Silicon in Dependence on Oxygen and Carbon Content', Phys.Stat.Sol.(a), Vol.77, No.2, 1983, pages 571 to 582	1-17
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